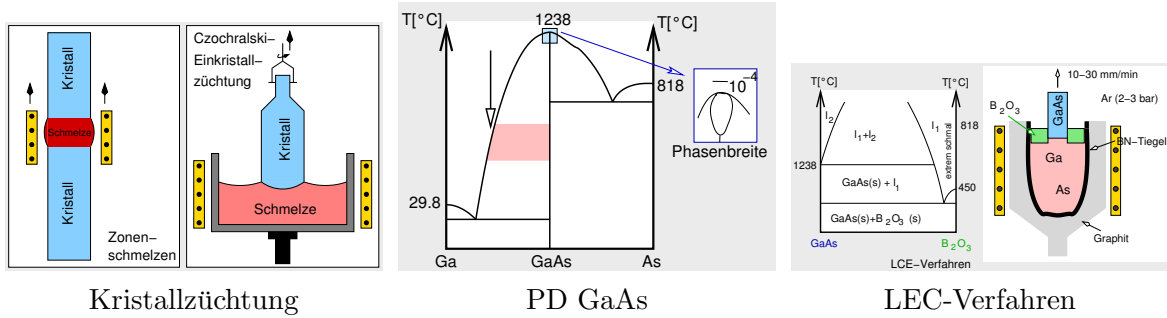


2.4.3. Herstellung von Halbleitern

2.4.3.1. Substratherstellung

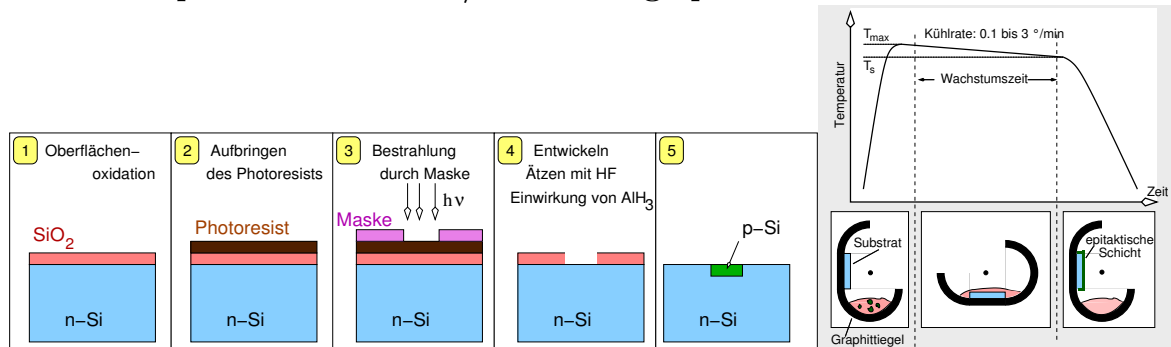


Kristallzuchtung

PD GaAs

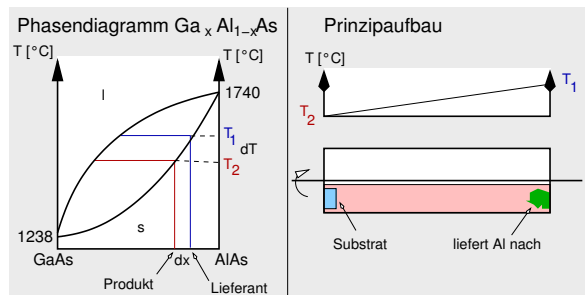
LEC-Verfahren

2.3.3.2. Depositionsverfahren/Herstellung epitaktischer Schichten

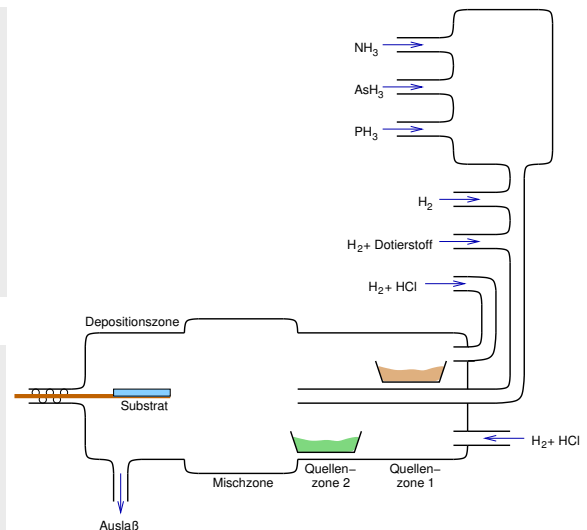
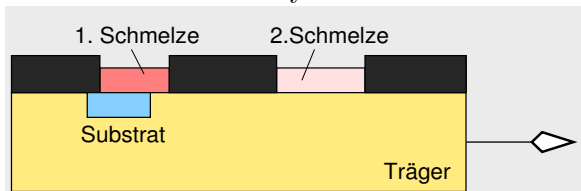


Diffusionsverfahren

LPE II: Tipping

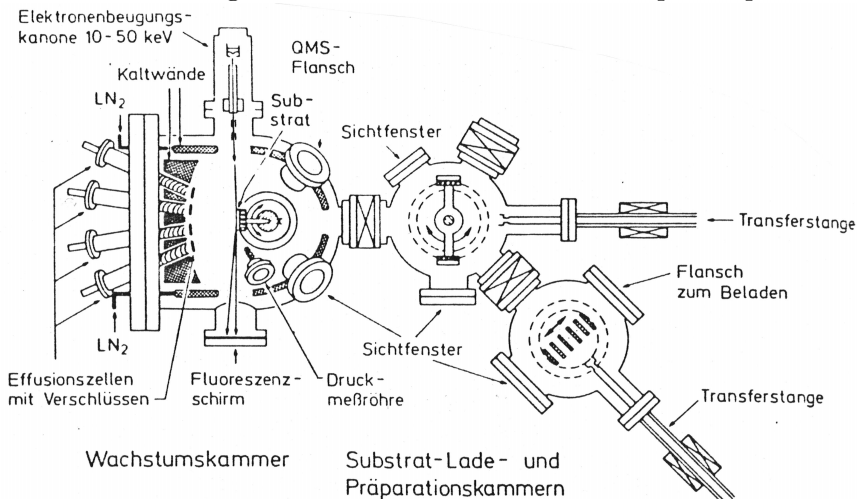


LPE III: Steady-State-Technik



Chemical Vapor Deposition (CVD)

LPE IV: Sliding



Molekularstrahl-Epitaxie (MBE)